

---

# PF0121

MOS FET Power Amplifier Module for GSM Mobile Phone

# HITACHI

ADE-208-097A (Z)  
2nd. Edition  
July 1996

---

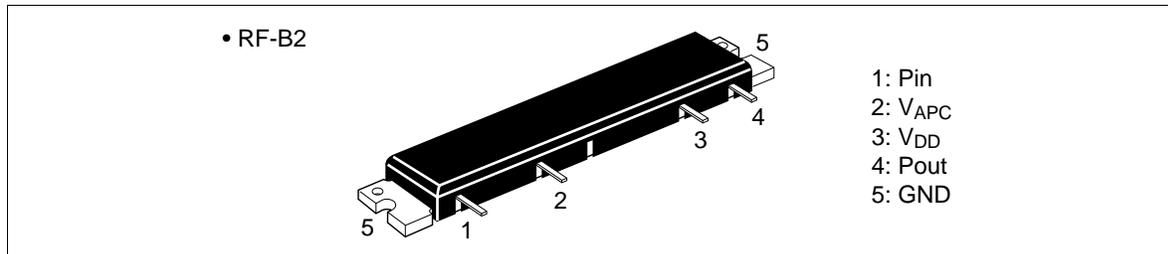
## Application

For GSM CLASS2 890 to 915 MHz

## Features

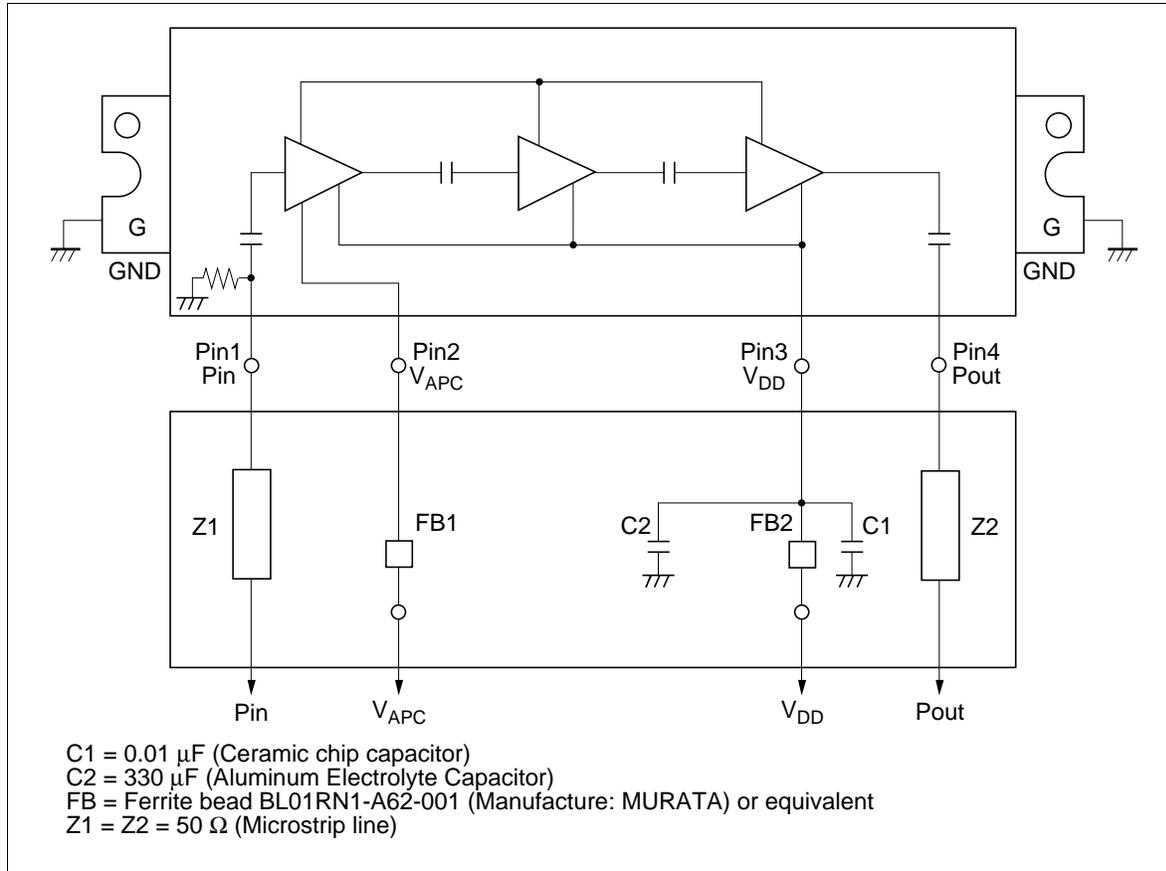
- Low power control current: 0.9 mA Typ
- High speed switching: 1.5  $\mu$ sec Typ
- Wide power control range: 100 dB Typ

## Pin Arrangement



# PF0121

## Internal Diagram and External Circuit



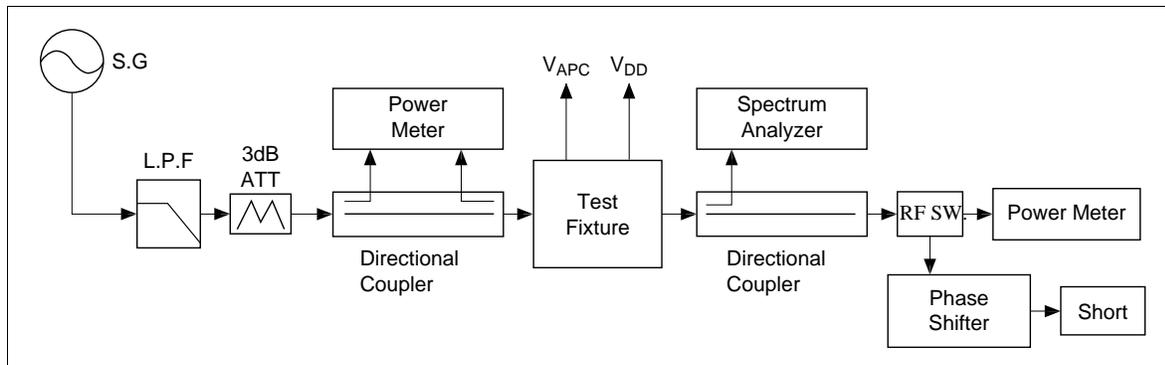
### Absolute Maximum Ratings ( $T_c = 25^\circ\text{C}$ )

Item	Symbol	Rating	Unit
Supply voltage	VDD	17	V
Supply current	IDD	6	A
APC voltage	VAPC	8	V
Input power	Pin	20	mW
Operating case temperature	$T_c$ (op)	-30 to +110	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-40 to +110	$^\circ\text{C}$

**Electrical Characteristics (Tc = 25°C)**

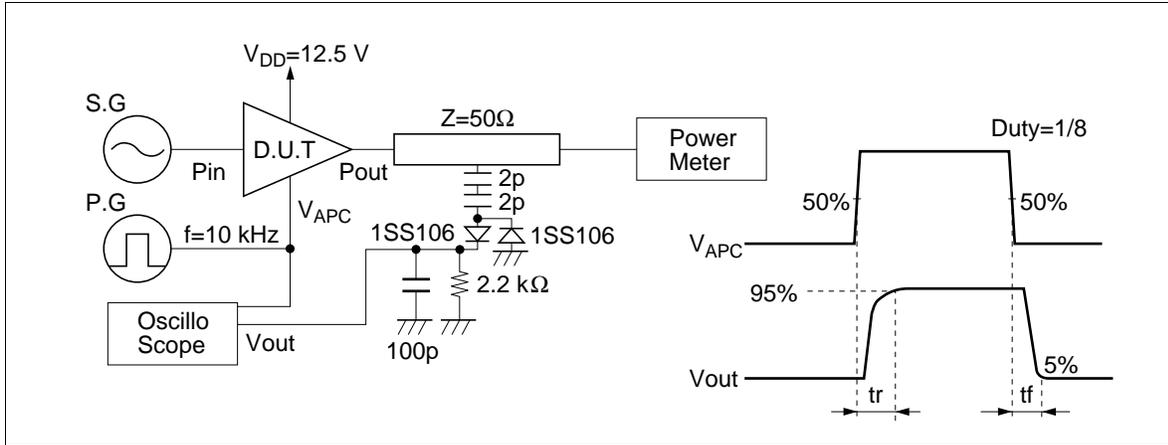
Item	Symbol	Min	Typ	Max	Unit	Test Condition
Drain cutoff current	IDS	—	—	500	μA	VDD = 17 V, VAPC = 0 V
Total efficiency	ηT	30	35	—	%	Pin = 2 mW, VDD = 12.5 V,
2nd harmonic distortion	2nd H.D.	—	-50	-40	dBc	Pout = 13 W (at APC controlled),
3rd harmonic distortion	3rd H.D.	—	-55	-45	dBc	RL = Rg = 50 Ω, Tc = 25°C
Input VSWR	VSWR (in)	—	2	3	—	
Output power (1)	Pout (1)	17	23	—	W	Pin = 2 mW, VDD = 12.5 V, VAPC = 7 V, RL = Rg = 50 Ω, Tc = 25°C
Output power (2)	Pout (2)	9	12	—	W	Pin = 2 mW, VDD = 10.3V, VAPC = 7 V, RL = Rg = 50 Ω, Tc = 80°C
Isolation	—	—	-60	-40	dBm	Pin = 2 mW, VDD = 12.5 V, VAPC = 0.5 V, RL = Rg = 50 Ω, Tc = 25°C
Switching time	tr, tf	—	1.5	2	μs	Pin = 2 mW, VDD = 12.5 V, Pout = 13 W, RL = Rg = 50 Ω, Tc = 25°C
Stability	—	No parasitic oscillation			—	Pin = 2 mW, VDD = 12.5 V, Pout ≤ 13 W (at APC controlled), Rg = 50 Ω, Tc = 25°C, Output VSWR = 20:1 All phases

**Test System Diagram**



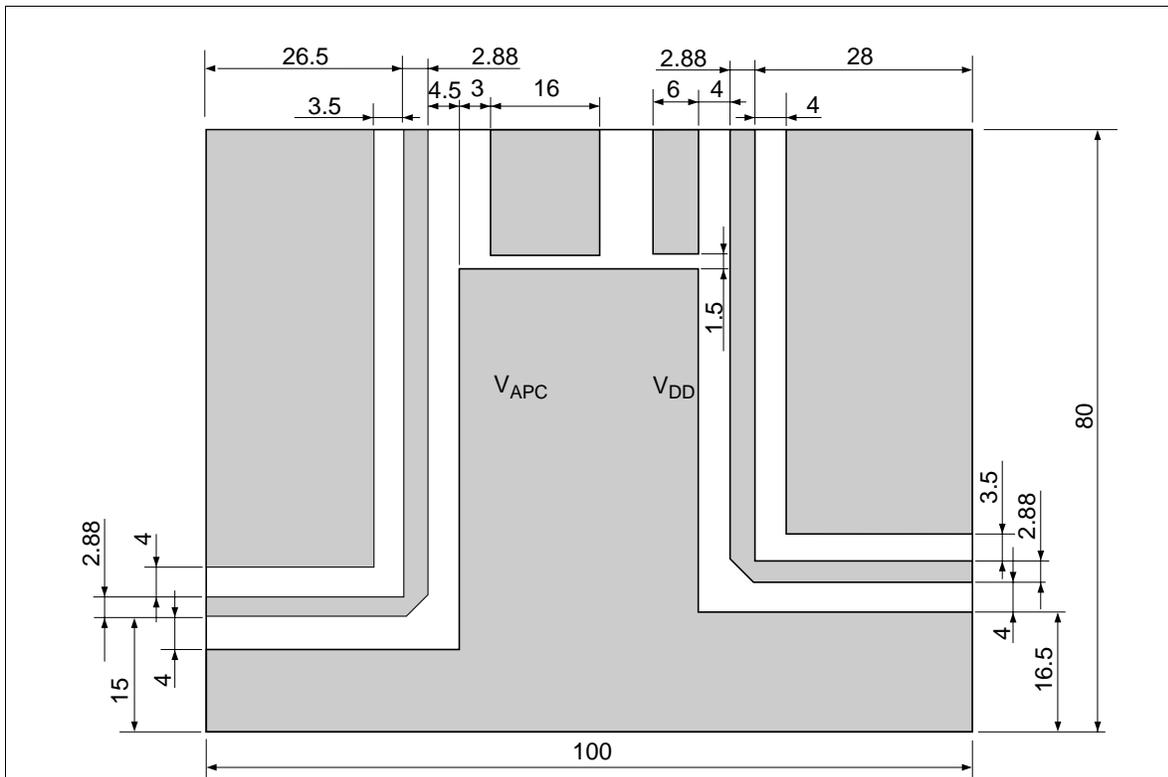
# PF0121

## Switching Time Test Diagram



## Test Fixture Pattern

Unit: mm



Grass Epoxy Double sided PCB

( $t = 1.6\text{ mm}$ ,  $\epsilon_r = 4.8$ )

C1=0.01 $\mu\text{F}$  (Ceramic Chip Capacitor)

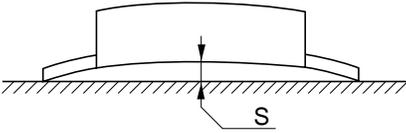
C2=330 $\mu\text{F}$  (Aluminum Electrolyte Capacitor)

L1=L2 : BLO2RN1-R62 (Manufacturer : MURATA) or equivalent (Ferrite Bead Inductor)

The coefficient of RF line loss in the P.C.B is showed bellow.

$$1/(S_{21})^2 = 1/(0.9805)^2 = 1.068$$

## Mechanical Characteristics

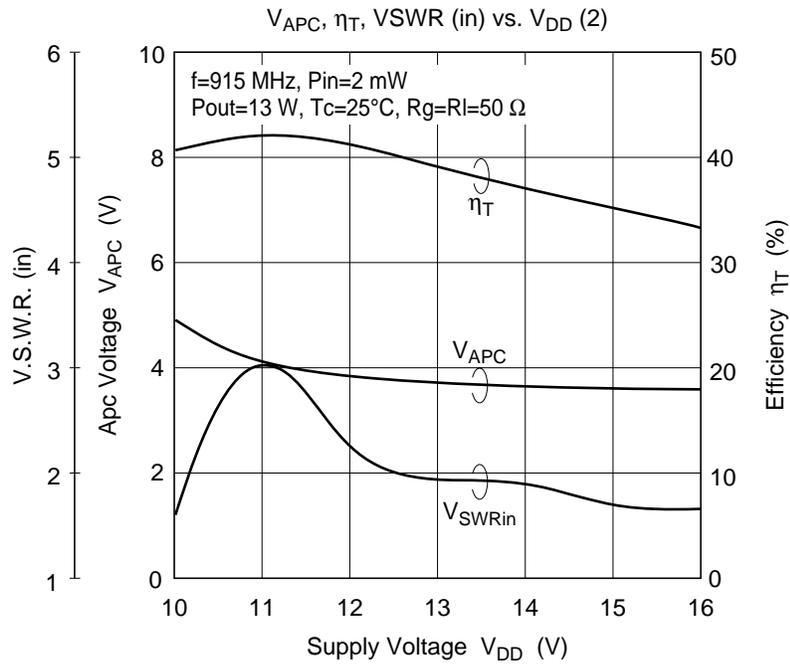
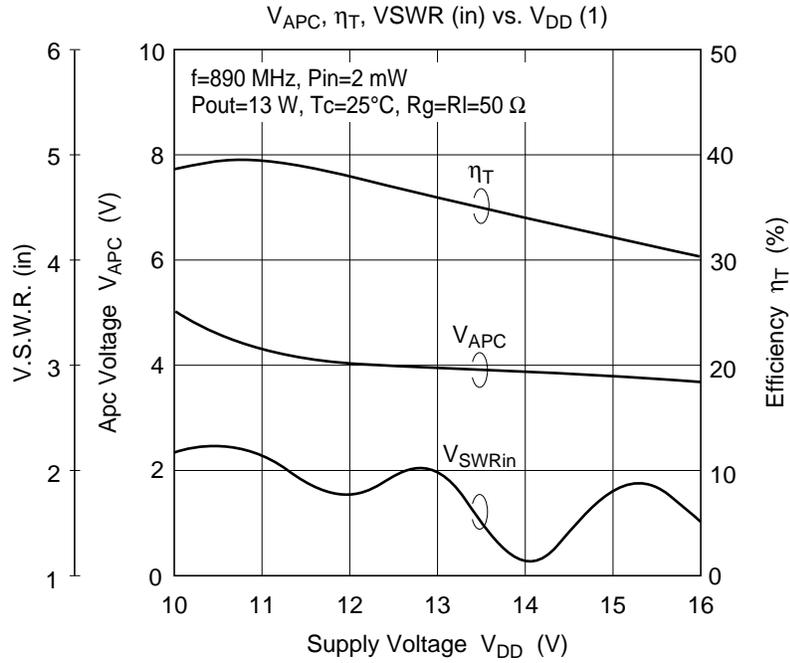
Item	Conditions	Spec
Torque for screw up the heatsink flange	M3 Screw Bolts	4 to 6 kg•cm
Warp size of the heatsink flange: S		S = 0 +0.3/-0 mm

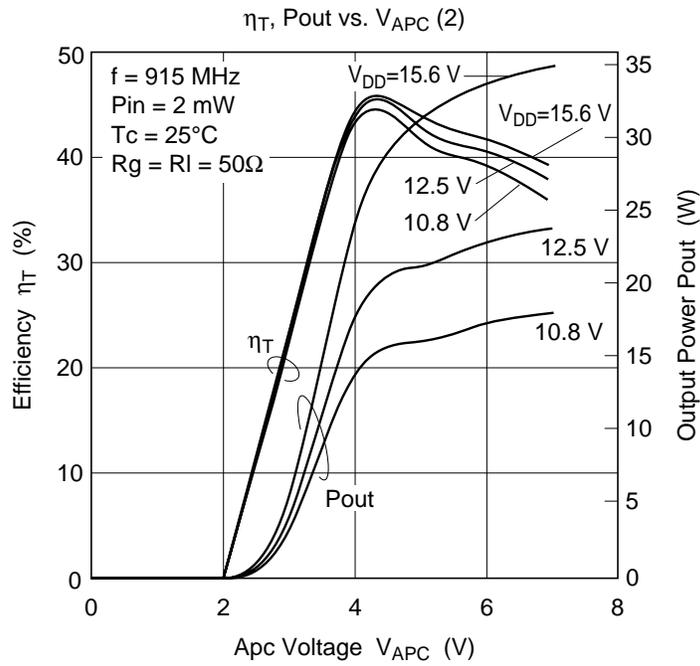
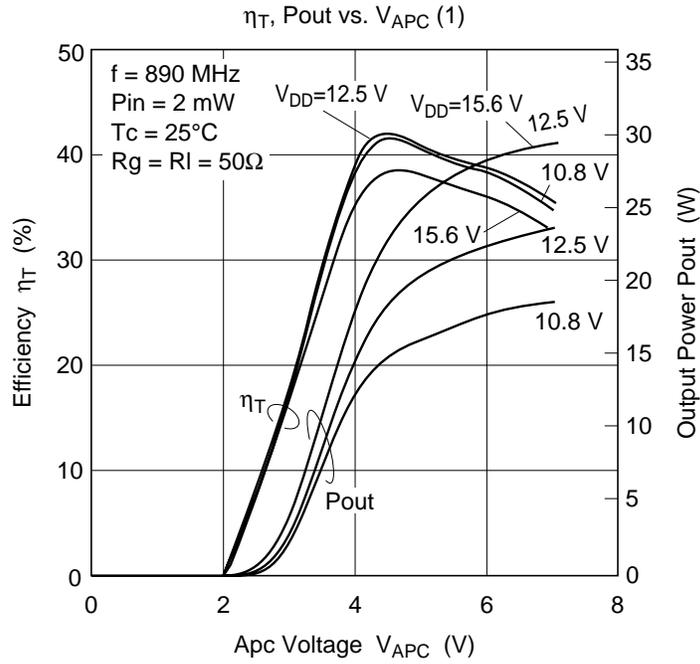
---

## Note for Use

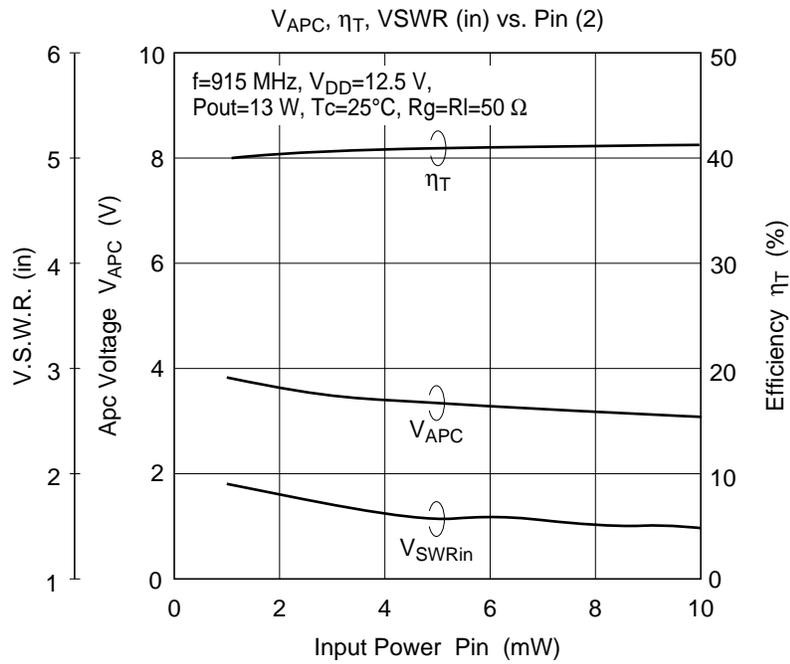
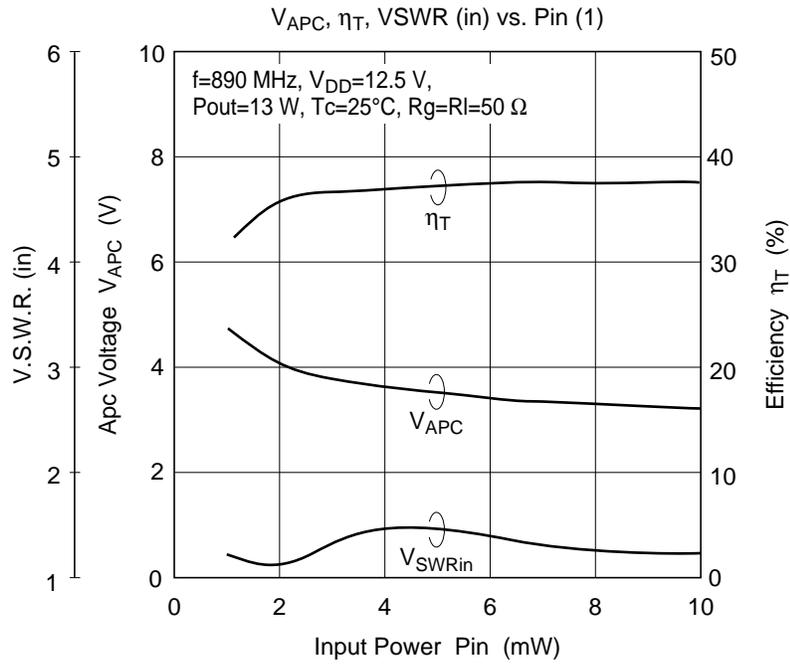
- Unevenness and distortion at the surface of the heatsink attached module should be less than 0.05 mm.
- It should not be existed any dust between module and heatsink.
- MODULE should be separated from PCB less than 1.5 mm.
- Soldering temperature and soldering time should be less than 230°C, 10 sec.  
(Soldering position spaced from the root point of the lead frame: 2 mm)
- Recommendation of thermal joint compounds is TYPE G746.  
(Manufacturer: Shin-Etsu Chemical, Co., Ltd.)
- To protect devices from electro-static damage, soldering iron, measuring-equipment and human body etc. should be grounded.
- Torque for screw up the heatsink flange should be 4 to 6 kg · cm with M3 screw bolts.
- Don't solder the flange directly.
- It should make the lead frame as straight as possible.
- The module should be screwed up before lead soldering.
- It should not be given mechanical and thermal stress to lead and flange of the module.
- When the external parts (Isolator, Duplexer, etc.) of the module are changed, the electrical characteristics should be evaluated enough.
- Don't washing the module except lead pins.
- To get good stability, ground impedance between the module GND flange and PCB GND pattern should be designed as low as possible.

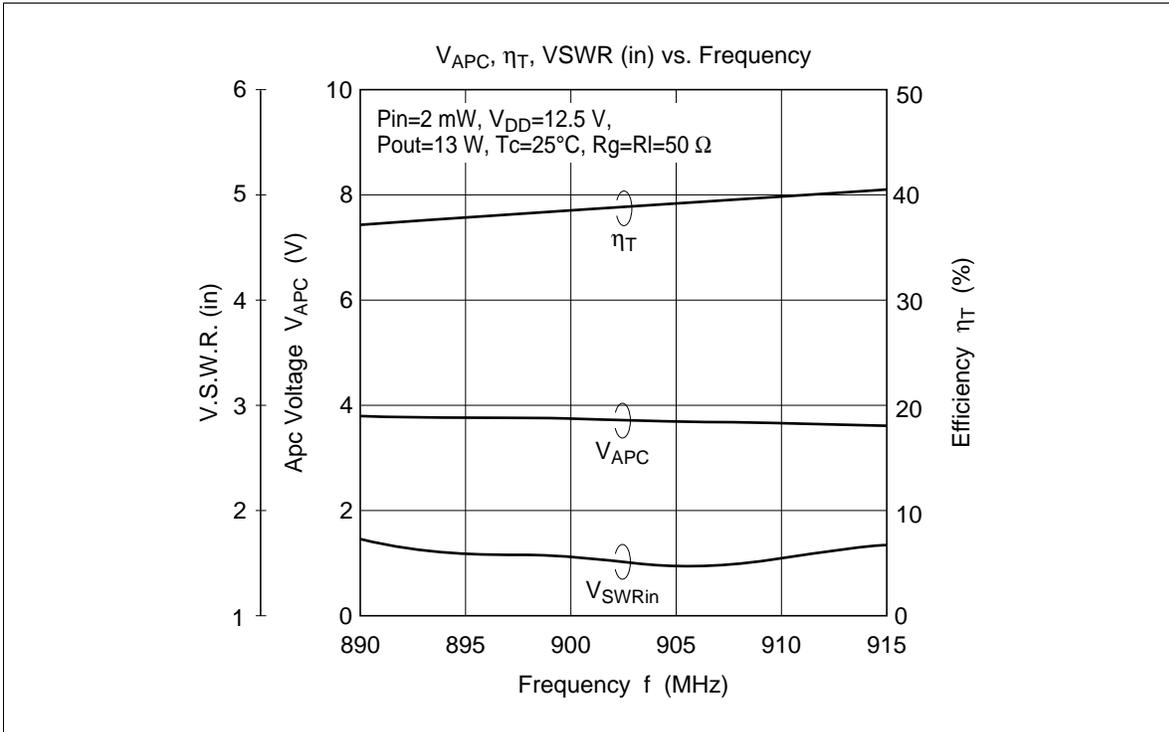
Characteristics Curve





# PF0121





# PF0121

## Package Dimensions

Unit: mm

